L	Hits	Search Text	DB	Time stamp
Number		(depolarization or (charge adj reduct?\$5)	USPAT;	2003/03/27
-	0	or (electrostatic adj discharge) or	US-PGPUB;	11:55
. }		(electrostatic adj discharge, of (electrostatic adj depolarization)) same	EPO; JPO;	
		(electrostatic adj depolalization)	DERWENT;	
İ	i	(plasma adj flood adj gun)	IBM TDB	
}		/ shawns add rodugt2\$5\	USPAT;	2003/03/27
-	237	(depolarization or (charge adj reduct?\$5)	US-PGPUB;	10:20
]		or (electrostatic adj discharge) or	EPO; JPO;	10.23
1		(electrostatic adj depolarization)) same	DERWENT;	
		plasma	IBM TDB	
			USPAT;	2003/03/27
-	4068	((depolarization or (charge adj	US-PGPUB;	10:21
		reduct?\$5) or (electrostatic adj	EPO; JPO;	10.21
· ·	,	discharge) or (electrostatic adj		
	1	depolarization)) same plasma) (wafer adj	DERWENT;	
	,	fabrication)	IBM_TDB	2003/03/27
_	30	((depolarization or (charge adj	USPAT;	10:25
		reduct?\$5) or (electrostatic adj	US-PGPUB;	10:25
		discharge) or (electrostatic adj	EPO; JPO;	Į.
	ļ	depolarization)) same plasma) and wafer	DERWENT;	
	ļ		IBM_TDB	0000 (00 (07
_	79	depolarization adj (method or process)	USPAT;	2003/03/27
	]	•	US-PGPUB;	10:25
			EPO; JPO;	
			DERWENT;	
	ļ .	•	IBM_TDB	
	90	((charge adj reduct?\$5) or	USPAT;	2003/03/27
-	)	depolarization) adj (method or process)	US-PGPUB;	10:26
		depotation, and the	EPO; JPO;	
		·	DERWENT;	
			IBM TDB	1
	_	(((charge adj reduct?\$5) or	USPAT;	2003/03/27
<del>-</del>		depolarization) adj (method or process))	US-PGPUB;	10:27
		and (expos?\$5 with plasma)	EPO; JPO;	
		and (exposito with prasma)	DERWENT;	
			IBM TDB	<u> </u>
	1,	(((charge adj reduct?\$5) or	USPAT;	2003/03/27
-	11	depolarization) adj (method or process))	US-PGPUB;	10:27
		depotarization, adj (method of process,	EPO; JPO;	İ
		and plasma	DERWENT;	
	1	. •	IBM TDB	
		(depolarization or (de adj polarization))	USPAT;	2003/03/27
i <del>-</del>	7553	(depotarization of (de ad) potarization,	US-PGPUB;	12:03
			EPO; JPO;	
			DERWENT;	
[			IBM TDB	
	_	// 1 1 /do add	USPAT;	2003/03/27
-	6	((depolarization or (de adj	US-PGPUB;	11:58
		polarization))) and (wafer adj	EPO; JPO;	
		fabricat?\$5)	DERWENT;	
1			IBM TDB	1
	1		USPAT;	2003/03/27
-	12	((electrostatic adj discharge) or esd)	US-PGPUB;	12:02
		with (wafer adj fabricat?\$5)	EPO; JPO;	12.02
1	ļ		1	
	1		DERWENT;	1
1	1		IBM_TDB	2003/03/27
-	0		USPAT;	12:03
1		adj fabricat?\$5)	US-PGPUB;	12.03
			EPO; JPO;	1
1			DERWENT;	
			IBM_TDB	0000/00/07
-	1		USPAT;	2003/03/27
		with (wafer adj fabricat?\$5)	US-PGPUB;	12:05
	1		EPO; JPO;	
1		1	DERWENT;	1
1	i.	1	IBM TDB	

	·	the formation and	USPAT;	2003/03/27
-	0	depolarization with (wafer near2 pad)	US-PGPUB;	12:08
		, , , , , , , , , , , , , , , , , , ,	EPO; JPO;	
	ĺ		DERWENT;	
	l		IBM_TDB	
ĺ	37	semiconductor adj fabrication adj tool?	USPAT;	2003/03/27
-	3, 1	Semiconductor day rames	US-PGPUB;	12:08
			EPO; JPO;	
		·	DERWENT;	
			IBM_TDB	2022/22/27
_	0	(semiconductor adj fabrication adj tool?)	USPAT;	2003/03/27
		with (discharge near2 electrostatic)	US-PGPUB;	12:10
			EPO; JPO;	]
	ì		DERWENT; IBM TDB	}
			USPAT;	2003/03/27
-	0	(semiconductor adj fabrication adj tool?)	US-PGPUB;	12:10
	ļ [	with ((discharge near2 electrostatic) or	EPO; JPO;	12.10
1		esd or (electrostatic adj discharge))	DERWENT;	
			IBM TDB	
		(semiconductor adj fabrication adj tool?)	USPAT;	2003/03/27
1 -	0	same ((discharge near2 electrostatic) or	US-PGPUB;	12:11
	9	esd or (electrostatic adj discharge))	EPO; JPO;	
		ead of leteoficacian and argenize 32/1	DERWENT;	
			IBM_TDB	
1_	207	(ion adj implantation) same	USPAT;	2003/03/27
-	20,	((electrostatic adj charge) or esd or	US-PGPUB;	12:12
İ		(electrostatic adj discharge))	EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	0000 (00 (07
_	41	((ion adj implantation) same	USPAT;	2003/03/27
		((electrostatic adj charge) or esd or	US-PGPUB;	12:12
		(electrostatic adj discharge))) and	EPO; JPO;	
		plasma	DERWENT; IBM TDB	
			USPAT;	2003/03/27
-	1	(wafer near2 pad) with (depolarization or	US-PGPUB;	12:45
		(de adj polarization) or (electrostatic adj discharge) or esd or (charge near2	EPO; JPO;	
		(reduct?\$5 or neutralization)))	DERWENT;	
		(leduct:42 of heatfallZactom//	IBM TDB	
	. 4	(("5089710") or ("5399871")).PN.	USPAT;	2003/03/27
-	1	(( 3003/20 / 52 ( 3344 2 //	US-PGPUB;	13:25
		<u>:</u>	EPO; JPO;	
	1		DERWENT;	'
			IBM_TDB	0000 (00 (07
-	0	("(insulating near2 pad) with	USPAT;	2003/03/27
	1	plasma").PN.	US-PGPUB;	14:36
			EPO; JPO; DERWENT;	
			IBM TDB	1
		/in malating many and with mlasma	USPAT;	2003/03/27
-	14	(insulating near2 pad) with plasma	US-PGPUB;	14:38
1			EPO; JPO;	
	-		DERWENT;	
	·		IBM TDB	
	118741	(H01L021/3065 or H01L021/205 or	USPAT;	2003/03/27
1 -	110/41	H01L021/31 or H01L021/68).ipc.	US-PGPUB;	14:39
			EPO; JPO;	
			DERWENT;	
	· ·		IBM_TDB	
_	23297	((H01L021/3065 or H01L021/205 or	USPAT;	2003/03/27
		H01L021/31 or H01L021/68).ipc.) and	US-PGPUB;	14:39
		plasma	EPO; JPO;	
		•	DERWENT;	
	1		IBM_TDB	
-	3	(((H01L021/3065 or H01L021/205 or	USPAT;	2003/03/27
	-	H01L021/31 or H01L021/68).ipc.) and	US-PGPUB;	14:39
,		plasma) and (insulating near3 pad?)	EPO; JPO;	
			DERWENT;	
		·	IBM TDB	